

PATENT  
740756 1986

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



in re PATENT application of:

Yasuhiko TAKEMURA

Application No.: 09/342,235

Filed: June 29, 1999

For: SEMICONDUCTOR DEVICE HAVING AT  
LEAST FIRST AND SECOND THIN FILM  
TRANSISTORS (As Amended)

Art Unit: 2826

Examiner: A. SEFER

AMENDMENT

Commissioner of Patents  
Washington, D.C. 20231

January 9, 2002  
(Wednesday)  
*[Signature]*

Dear Sir:

In response to the Examiner's non-Final Office Action mailed August 9, 2001, please consider the following amendments and remarks in connection with the above-identified application.

IN THE CLAIMS:

Please amend claims 9 and 11 to read as follows:

9. (Amended) A semiconductor device comprising:

a substrate having an insulating surface;

at least first and second semiconductor islands formed over said substrate wherein each of the semiconductor islands has a channel region and a pair of impurity regions;

an insulating film formed over said substrate, said insulating film including at least first and second gate insulating films formed over said first and second semiconductor islands, respectively;